

AMENDMENTS TO THE SPECIFICATION

Please replace the paragraph beginning on page 3, line 15 with the following paragraph:

[0007] Multi-layer structure 5 includes a semiconductor substrate ~~10~~ 12 that is formed of undoped GaAs. Disposed in successive layers over semiconductor substrate 12 are various epitaxial semiconductor layers, including: a buffer layer 14; channel and spacer layers 16; an E-mode barrier layer 18; an E-mode etch stop layer 20; a D-mode barrier layer 22; a D-mode etch stop 24; a wide recess transition layer 26; and an ohmic contact layer 28. Note that there are two barrier layers and two etch stop layers.